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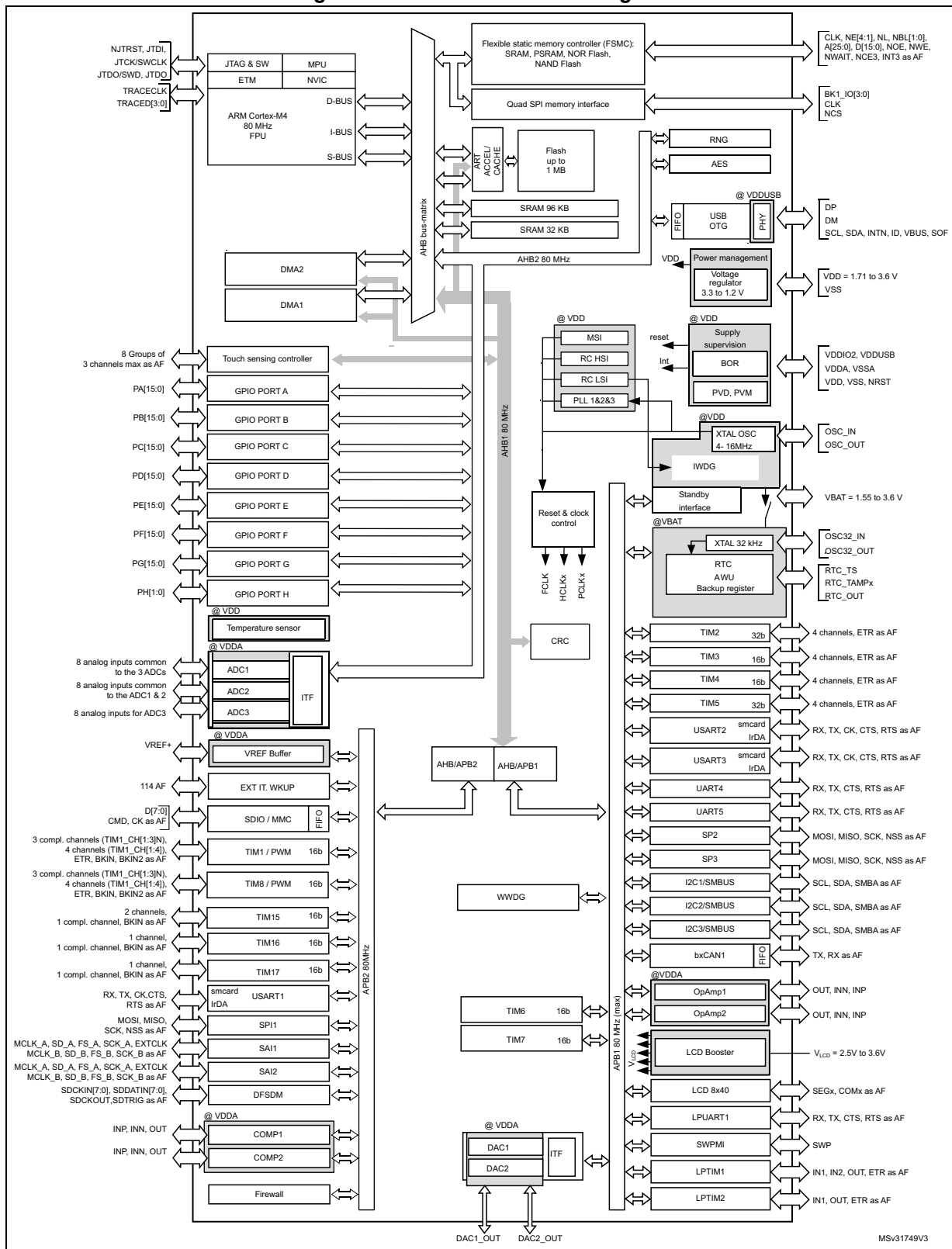
"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	80MHz
Connectivity	CANbus, I ² C, IrDA, LINbus, MMC/SD, QSPI, SAI, SPI, SWPMI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, LCD, PWM, WDT
Number of I/O	51
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	128K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l486rgt7tr

Figure 1. STM32L486xx block diagram



Note: *AF: alternate function on I/O pins.*

Table 5. Functionalities depending on the working mode⁽¹⁾

Peripheral	Run	Sleep	Low-power run	Low-power sleep	Stop 0/1		Stop 2		Standby		Shutdown		VBAT
					-	Wakeup capability	-	Wakeup capability	-	Wakeup capability	-	Wakeup capability	
CPU	Y	-	Y	-	-	-	-	-	-	-	-	-	-
Flash memory (1 MB)	O ⁽²⁾	O ⁽²⁾	O ⁽²⁾	O ⁽²⁾	-	-	-	-	-	-	-	-	-
SRAM1 (96 KB)	Y	Y ⁽³⁾	Y	Y ⁽³⁾	Y	-	Y	-	-	-	-	-	-
SRAM2 (32 KB)	Y	Y ⁽³⁾	Y	Y ⁽³⁾	Y	-	Y	-	O ⁽⁴⁾	-	-	-	-
FSMC	O	O	O	O	-	-	-	-	-	-	-	-	-
Quad SPI	O	O	O	O	-	-	-	-	-	-	-	-	-
Backup Registers	Y	Y	Y	Y	Y	-	Y	-	Y	-	Y	-	Y
Brown-out reset (BOR)	Y	Y	Y	Y	Y	Y	Y	Y	Y	Y	-	-	-
Programmable Voltage Detector (PVD)	O	O	O	O	O	O	O	O	-	-	-	-	-
Peripheral Voltage Monitor (PVMx; x=1,2,3,4)	O	O	O	O	O	O	O	O	-	-	-	-	-
DMA	O	O	O	O	-	-	-	-	-	-	-	-	-
High Speed Internal (HSI16)	O	O	O	O	(5)	-	(5)	-	-	-	-	-	-
High Speed External (HSE)	O	O	O	O	-	-	-	-	-	-	-	-	-
Low Speed Internal (LSI)	O	O	O	O	O	-	O	-	O	-	-	-	-
Low Speed External (LSE)	O	O	O	O	O	-	O	-	O	-	O	-	O
Multi-Speed Internal (MSI)	O	O	O	O	-	-	-	-	-	-	-	-	-
Clock Security System (CSS)	O	O	O	O	-	-	-	-	-	-	-	-	-
Clock Security System on LSE	O	O	O	O	O	O	O	O	O	O	-	-	-
RTC / Auto wakeup	O	O	O	O	O	O	O	O	O	O	O	O	O
Number of RTC Tamper pins	3	3	3	3	3	O	3	O	3	O	3	O	3
LCD	O	O	O	O	O	O	O	O	-	-	-	-	-

Table 5. Functionalities depending on the working mode⁽¹⁾ (continued)

Peripheral	Run	Sleep	Low-power run	Low-power sleep	Stop 0/1		Stop 2		Standby		Shutdown		VBAT
					-	Wakeup capability	-	Wakeup capability	-	Wakeup capability	-	Wakeup capability	
USB OTG FS	O ⁽⁸⁾	O ⁽⁸⁾	-	-	-	O	-	-	-	-	-	-	-
USARTx (x=1,2,3,4,5)	O	O	O	O	O ⁽⁶⁾	O ⁽⁶⁾	-	-	-	-	-	-	-
Low-power UART (LPUART)	O	O	O	O	O ⁽⁶⁾	O ⁽⁶⁾	O ⁽⁶⁾	O ⁽⁶⁾	-	-	-	-	-
I2Cx (x=1,2)	O	O	O	O	O ⁽⁷⁾	O ⁽⁷⁾	-	-	-	-	-	-	-
I2C3	O	O	O	O	O ⁽⁷⁾	O ⁽⁷⁾	O ⁽⁷⁾	O ⁽⁷⁾	-	-	-	-	-
SPIx (x=1,2,3)	O	O	O	O	-	-	-	-	-	-	-	-	-
CAN	O	O	O	O	-	-	-	-	-	-	-	-	-
SDMMC1	O	O	O	O	-	-	-	-	-	-	-	-	-
SWPMI1	O	O	O	O	-	O	-	-	-	-	-	-	-
SAIx (x=1,2)	O	O	O	O	-	-	-	-	-	-	-	-	-
DFSDM1	O	O	O	O	-	-	-	-	-	-	-	-	-
ADCx (x=1,2,3)	O	O	O	O	-	-	-	-	-	-	-	-	-
DACx (x=1,2)	O	O	O	O	O	-	-	-	-	-	-	-	-
VREFBUF	O	O	O	O	O	-	-	-	-	-	-	-	-
OPAMPx (x=1,2)	O	O	O	O	O	-	-	-	-	-	-	-	-
COMPx (x=1,2)	O	O	O	O	O	O	O	O	-	-	-	-	-
Temperature sensor	O	O	O	O	-	-	-	-	-	-	-	-	-
Timers (TIMx)	O	O	O	O	-	-	-	-	-	-	-	-	-
Low-power timer 1 (LPTIM1)	O	O	O	O	O	O	O	O	-	-	-	-	-
Low-power timer 2 (LPTIM2)	O	O	O	O	O	O	-	-	-	-	-	-	-
Independent watchdog (IWDG)	O	O	O	O	O	O	O	O	O	O	-	-	-
Window watchdog (WWDG)	O	O	O	O	-	-	-	-	-	-	-	-	-
SysTick timer	O	O	O	O	-	-	-	-	-	-	-	-	-
Touch sensing controller (TSC)	O	O	O	O	-	-	-	-	-	-	-	-	-
Random number generator (RNG)	O ⁽⁸⁾	O ⁽⁸⁾	-	-	-	-	-	-	-	-	-	-	-

interrupt is generated if enabled. LSE failure can also be detected and generated an interrupt.

- Clock-out capability:
 - **MCO: microcontroller clock output:** it outputs one of the internal clocks for external use by the application
 - **LSCO: low speed clock output:** it outputs LSI or LSE in all low-power modes (except VBAT).

Several prescalers allow to configure the AHB frequency, the high speed APB (APB2) and the low speed APB (APB1) domains. The maximum frequency of the AHB and the APB domains is 80 MHz.

All comparators can wake up from Stop mode, generate interrupts and breaks for the timers and can be also combined into a window comparator.

3.19 Operational amplifier (OPAMP)

The STM32L486xx embeds two operational amplifiers with external or internal follower routing and PGA capability.

The operational amplifier features:

- Low input bias current
- Low offset voltage
- Low-power mode
- Rail-to-rail input

3.20 Touch sensing controller (TSC)

The touch sensing controller provides a simple solution for adding capacitive sensing functionality to any application. Capacitive sensing technology is able to detect finger presence near an electrode which is protected from direct touch by a dielectric (glass, plastic, ...). The capacitive variation introduced by the finger (or any conductive object) is measured using a proven implementation based on a surface charge transfer acquisition principle.

The touch sensing controller is fully supported by the STMTouch touch sensing firmware library which is free to use and allows touch sensing functionality to be implemented reliably in the end application.

The main features of the touch sensing controller are the following:

- Proven and robust surface charge transfer acquisition principle
- Supports up to 24 capacitive sensing channels
- Up to 3 capacitive sensing channels can be acquired in parallel offering a very good response time
- Spread spectrum feature to improve system robustness in noisy environments
- Full hardware management of the charge transfer acquisition sequence
- Programmable charge transfer frequency
- Programmable sampling capacitor I/O pin
- Programmable channel I/O pin
- Programmable max count value to avoid long acquisition when a channel is faulty
- Dedicated end of acquisition and max count error flags with interrupt capability
- One sampling capacitor for up to 3 capacitive sensing channels to reduce the system components
- Compatible with proximity, touchkey, linear and rotary touch sensor implementation
- Designed to operate with STMTouch touch sensing firmware library

Note: The number of capacitive sensing channels is dependent on the size of the packages and subject to I/O availability.

Table 10. Timer feature comparison (continued)

Timer type	Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/compare channels	Complementary outputs
General-purpose	TIM16, TIM17	16-bit	Up	Any integer between 1 and 65536	Yes	1	1
Basic	TIM6, TIM7	16-bit	Up	Any integer between 1 and 65536	Yes	0	No

3.25.1 Advanced-control timer (TIM1, TIM8)

The advanced-control timer can each be seen as a three-phase PWM multiplexed on 6 channels. They have complementary PWM outputs with programmable inserted dead-times. They can also be seen as complete general-purpose timers. The 4 independent channels can be used for:

- Input capture
- Output compare
- PWM generation (edge or center-aligned modes) with full modulation capability (0-100%)
- One-pulse mode output

In debug mode, the advanced-control timer counter can be frozen and the PWM outputs disabled to turn off any power switches driven by these outputs.

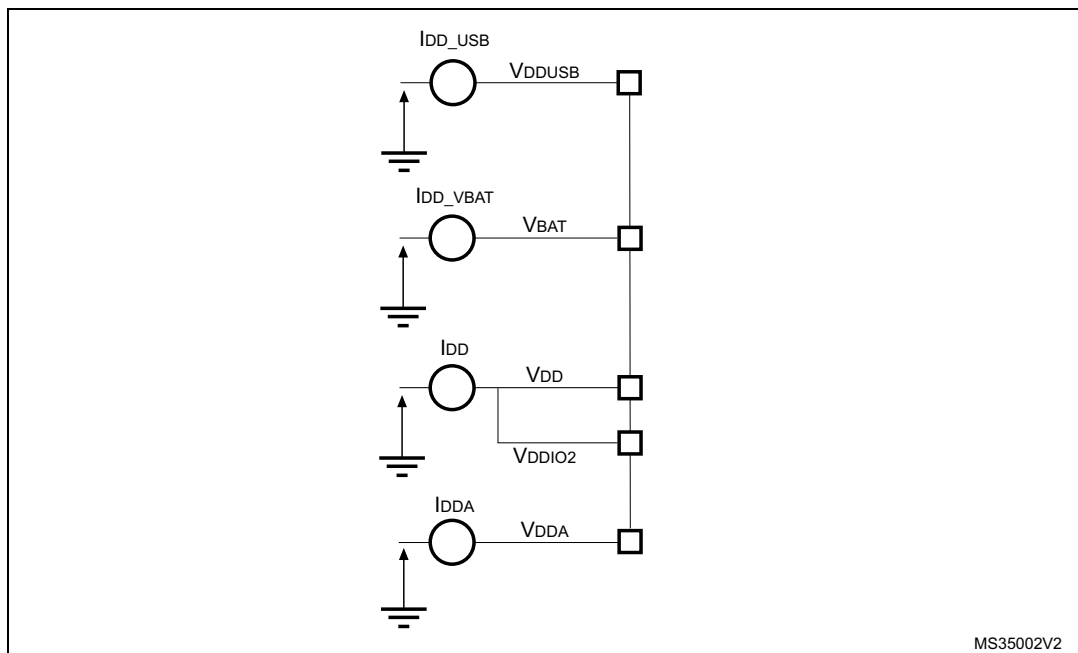
Many features are shared with those of the general-purpose TIMx timers (described in [Section 3.25.2](#)) using the same architecture, so the advanced-control timers can work together with the TIMx timers via the Timer Link feature for synchronization or event chaining.

Table 17. Alternate function AF8 to AF15 (for AF0 to AF7 see [Table 16](#)) (continued)

Port		AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		UART4, UART5, LPUART1	CAN1, TSC	OTG_FS, QUADSPI	LCD	SDMMC1, COMP1, COMP2, FMC, SWPMI1	SAI1, SAI2	TIM2, TIM15, TIM16, TIM17, LPTIM2	EVENTOUT
Port H	PH0	-	-	-	-	-	-	-	EVENTOUT
	PH1	-	-	-	-	-	-	-	EVENTOUT

6.1.7 Current consumption measurement

Figure 14. Current consumption measurement scheme



6.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in [Table 19: Voltage characteristics](#), [Table 20: Current characteristics](#) and [Table 21: Thermal characteristics](#) may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Table 19. Voltage characteristics⁽¹⁾

Symbol	Ratings	Min	Max	Unit
$V_{DDX} - V_{SS}$	External main supply voltage (including V_{DD} , V_{DDA} , V_{DDIO2} , V_{DDUSB} , V_{LCD} , V_{BAT})	-0.3	4.0	V
$V_{IN}^{(2)}$	Input voltage on FT_XXX pins	$V_{SS}-0.3$	$\min(V_{DD}, V_{DDA}, V_{DDIO2}, V_{DDUSB}, V_{LCD}) + 4.0^{(3)(4)}$	V
	Input voltage on TT_XX pins	$V_{SS}-0.3$	4.0	
	Input voltage on BOOT0 pin	V_{SS}	9.0	
	Input voltage on any other pins	$V_{SS}-0.3$	4.0	
$ \Delta V_{DDx} $	Variations between different V_{DDx} power pins of the same domain	-	50	mV
$ V_{SSx}-V_{SS} $	Variations between all the different ground pins ⁽⁵⁾	-	50	mV

1. All main power (V_{DD} , V_{DDA} , V_{DDIO2} , V_{DDUSB} , V_{LCD} , V_{BAT}) and ground (V_{SS} , V_{SSA}) pins must always be connected to the external power supply, in the permitted range.

Table 35. Current consumption in Stop 1 mode

Symbol	Parameter	Conditions			TYP					MAX ⁽¹⁾					Unit
		-	-	V _{DD}	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C	125 °C	
I _{DD} (Stop 1)	Supply current in Stop 1 mode, RTC disabled	-	LCD disabled	1.8 V	6.59	24.7	92.7	208	437	16	62	232	520	1093	µA
				2.4 V	6.65	24.8	92.9	209	439	17	62	232	523	1098	
				3 V	6.65	24.9	93.3	210	442	17	62	233	525	1105	
				3.6 V	6.70	25.1	93.8	212	447	17	63	235	530	1118	
		-	LCD enabled ⁽²⁾ clocked by LSI	1.8 V	7.00	25.2	97.2	219	461	18	63	243	548	1153	
				2.4 V	7.14	25.4	97.5	220	463	18	64	244	550	1158	
				3 V	7.24	25.7	97.7	221	465	18	64	244	553	1163	
				3.6 V	7.36	26.1	98.7	223	471	18	65	247	558	1178	
I _{DD} (Stop 1 with RTC)	Supply current in stop 1 mode, RTC enabled	RTC clocked by LSI	LCD disabled	1.8 V	6.88	25.0	93.1	209	439	17	63	233	523	1098	µA
				2.4 V	7.02	25.2	93.7	210	441	18	63	234	525	1103	
				3 V	7.12	25.4	94.2	212	444	18	64	236	530	1110	
				3.6 V	7.25	25.7	95.2	214	449	18	64	238	535	1123	
			LCD enabled ⁽²⁾	1.8 V	7.01	26.1	99.0	223	467	18	65	248	558	1168	
				2.4 V	7.14	26.3	99.6	225	470	18	66	249	563	1175	
				3 V	7.31	26.6	100.0	226	474	18	67	250	565	1185	
				3.6 V	7.41	26.9	102.0	229	480	19	67	255	573	1200	
		RTC clocked by LSE bypassed at 32768 Hz	LCD disabled	1.8 V	6.91	25.2	93.4	210	440	17	63	234	525	1100	
				2.4 V	7.04	25.3	94.2	211	443	18	63	236	528	1108	
				3 V	7.19	25.7	95.0	212	446	18	64	238	530	1115	
				3.6 V	7.97	26.0	96.1	215	451	20	65	240	538	1128	
		RTC clocked by LSE quartz ⁽³⁾ in low drive mode	LCD disabled	1.8 V	6.85	25.0	93.0	208.3	-	17	63	233	521	-	
				2.4 V	6.94	25.1	93.2	209.3	-	17	63	233	523	-	
				3 V	7.10	25.2	93.6	210.3	-	18	63	234	526	-	
				3.6 V	7.34	25.4	94.1	212.3	-	18	64	235	531	-	

Multi-speed internal (MSI) RC oscillator

Table 49. MSI oscillator characteristics⁽¹⁾

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
f_{MSI}	MSI frequency after factory calibration, done at $V_{\text{DD}}=3\text{ V}$ and $T_{\text{A}}=30\text{ }^{\circ}\text{C}$	MSI mode	Range 0	99	100	101	kHz
			Range 1	198	200	202	
			Range 2	396	400	404	
			Range 3	792	800	808	
			Range 4	0.99	1	1.01	MHz
			Range 5	1.98	2	2.02	
			Range 6	3.96	4	4.04	
			Range 7	7.92	8	8.08	
			Range 8	15.8	16	16.16	
			Range 9	23.8	24	24.4	
			Range 10	31.7	32	32.32	
			Range 11	47.5	48	48.48	
		PLL mode XTAL= 32.768 kHz	Range 0	-	98.304	-	kHz
			Range 1	-	196.608	-	
			Range 2	-	393.216	-	
			Range 3	-	786.432	-	
			Range 4	-	1.016	-	MHz
			Range 5	-	1.999	-	
			Range 6	-	3.998	-	
			Range 7	-	7.995	-	
			Range 8	-	15.991	-	
			Range 9	-	23.986	-	
			Range 10	-	32.014	-	
			Range 11	-	48.005	-	
$\Delta_{\text{TEMP}}(\text{MSI})^{(2)}$	MSI oscillator frequency drift over temperature	MSI mode	$T_{\text{A}} = -0\text{ to }85\text{ }^{\circ}\text{C}$	-3.5	-	3	%
			$T_{\text{A}} = -40\text{ to }125\text{ }^{\circ}\text{C}$	-8	-	6	

Table 69. ADC accuracy - limited test conditions 4⁽¹⁾⁽²⁾⁽³⁾

Sym- bol	Parameter	Conditions ⁽⁴⁾		Min	Typ	Max	Unit
ET	Total unadjusted error	Single ended	Fast channel (max speed)	-	5	5.4	LSB
			Slow channel (max speed)	-	4	5	
		Differential	Fast channel (max speed)	-	4	5	
			Slow channel (max speed)	-	3.5	4.5	
EO	Offset error	Single ended	Fast channel (max speed)	-	2	4	
			Slow channel (max speed)	-	2	4	
		Differential	Fast channel (max speed)	-	2	3.5	
			Slow channel (max speed)	-	2	3.5	
EG	Gain error	Single ended	Fast channel (max speed)	-	4	4.5	
			Slow channel (max speed)	-	4	4.5	
		Differential	Fast channel (max speed)	-	3	4	
			Slow channel (max speed)	-	3	4	
ED	Differential linearity error	Single ended	Fast channel (max speed)	-	1	1.5	
			Slow channel (max speed)	-	1	1.5	
		Differential	Fast channel (max speed)	-	1	1.2	
			Slow channel (max speed)	-	1	1.2	
EL	Integral linearity error	Single ended	Fast channel (max speed)	-	2.5	3	
			Slow channel (max speed)	-	2.5	3	
		Differential	Fast channel (max speed)	-	2	2.5	
			Slow channel (max speed)	-	2	2.5	
ENOB	Effective number of bits	Single ended	Fast channel (max speed)	10.2	10.5	-	bits
			Slow channel (max speed)	10.2	10.5	-	
		Differential	Fast channel (max speed)	10.6	10.7	-	
			Slow channel (max speed)	10.6	10.7	-	
SINAD	Signal-to-noise and distortion ratio	Single ended	Fast channel (max speed)	63	65	-	dB
			Slow channel (max speed)	63	65	-	
		Differential	Fast channel (max speed)	65	66	-	
			Slow channel (max speed)	65	66	-	
SNR	Signal-to-noise ratio	Single ended	Fast channel (max speed)	64	65	-	
			Slow channel (max speed)	64	65	-	
		Differential	Fast channel (max speed)	66	67	-	
			Slow channel (max speed)	66	67	-	

Table 69. ADC accuracy - limited test conditions 4⁽¹⁾(2)(3) (continued)

Sym- bol	Parameter	Conditions ⁽⁴⁾			Min	Typ	Max	Unit
THD	Total harmonic distortion	ADC clock frequency \leq 26 MHz, $1.65\text{ V} \leq V_{\text{DDA}} = V_{\text{REF+}} \leq 3.6\text{ V}$, Voltage scaling Range 2	Single ended	Fast channel (max speed)	-	-71	-69	dB
				Slow channel (max speed)	-	-71	-69	
			Differential	Fast channel (max speed)	-	-73	-72	
				Slow channel (max speed)	-	-73	-72	

1. Guaranteed by design.
2. ADC DC accuracy values are measured after internal calibration.
3. ADC accuracy vs. negative Injection Current: Injecting negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative current.
4. The I/O analog switch voltage booster is enable when $V_{\text{DDA}} < 2.4\text{ V}$ (BOOSTEN = 1 in the SYSCFG_CFGR1 when $V_{\text{DDA}} < 2.4\text{ V}$). It is disable when $V_{\text{DDA}} \geq 2.4\text{ V}$. No oversampling.

Table 72. VREFBUF characteristics⁽¹⁾ (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$I_{DDA}(VREFBUF)$	VREFBUF consumption from V_{DDA}	$I_{load} = 0 \mu A$	-	16	25	μA
		$I_{load} = 500 \mu A$	-	18	30	
		$I_{load} = 4 mA$	-	35	50	

1. Guaranteed by design, unless otherwise specified.
2. In degraded mode, the voltage reference buffer can not maintain accurately the output voltage which will follow (V_{DDA} - drop voltage).
3. Guaranteed by test in production.
4. The capacitive load must include a 100 nF capacitor in order to cut-off the high frequency noise.
5. To correctly control the VREFBUF inrush current during start-up phase and scaling change, the V_{DDA} voltage should be in the range [2.4 V to 3.6 V] and [2.8 V to 3.6 V] respectively for $V_{RS} = 0$ and $V_{RS} = 1$.

6.3.25 DFSDM characteristics

Unless otherwise specified, the parameters given in [Table 79](#) for DFSDM are derived from tests performed under the ambient temperature, f_{APB2} frequency and V_{DD} supply voltage conditions summarized in [Table 22: General operating conditions](#).

- Output speed is set to $OSPEEDRy[1:0] = 10$
- Capacitive load $C = 30$ pF
- Measurement points are done at CMOS levels: $0.5 \times V_{DD}$

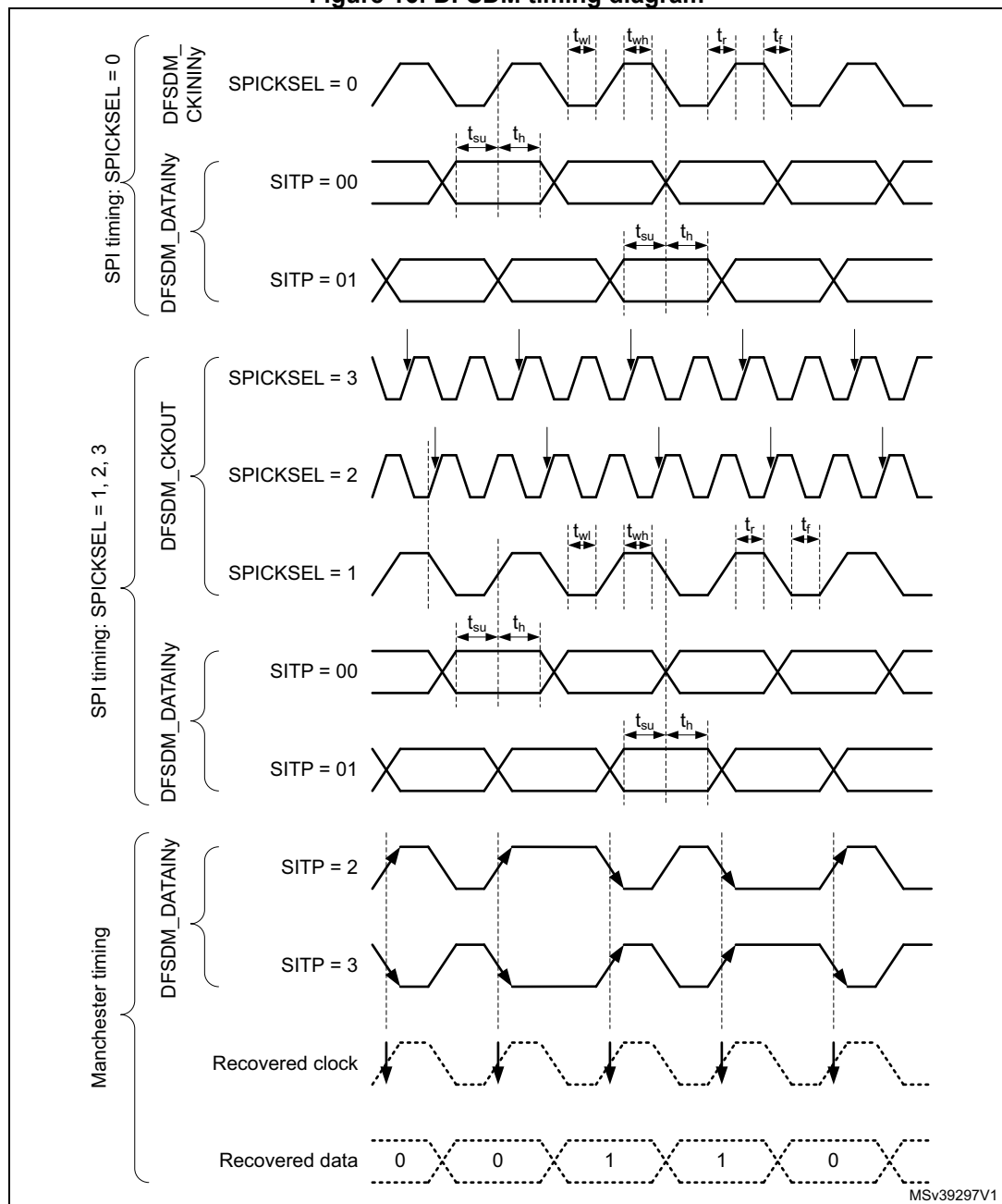
Refer to [Section 6.3.14: I/O port characteristics](#) for more details on the input/output alternate function characteristics (DFSDM1_CKINy, DFSDM1_DATINy, DFSDM1_CKOUT for DFSDM).

Table 79. DFSDM characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$f_{DFSDMCLK}$	DFSDM clock	-	-	-	f_{SYSCLK}	MHz
f_{CKIN} ($1/T_{CKIN}$)	Input clock frequency	SPI mode (SITP[1:0] = 01)	-	-	20 ($f_{DFSDMCLK}/4$)	
f_{CKOUT}	Output clock frequency	-	-	-	20	MHz
$DuCy_{CKOUT}$	Output clock frequency duty cycle	-	45	50	55	%
$t_{wh(CKIN)}$ $t_{wl(CKIN)}$	Input clock high and low time	SPI mode (SITP[1:0] = 01), External clock mode (SPICKSEL[1:0] = 0)	$T_{CKIN}/2-0.5$	$T_{CKIN}/2$	-	ns
t_{su}	Data input setup time	SPI mode (SITP[1:0]=01), External clock mode (SPICKSEL[1:0] = 0)	0	-	-	
t_h	Data input hold time	SPI mode (SITP[1:0]=01), External clock mode (SPICKSEL[1:0] = 0)	2	-	-	
$T_{Manchester}$	Manchester data period (recovered clock period)	Manchester mode (SITP[1:0] = 10 or 11), Internal clock mode (SPICKSEL[1:0] \neq 0)	$(CKOUT DIV+1) \times T_{DFSDMCLK}$	-	$(2 \times CKOUTDIV) \times T_{DFSDMCLK}$	

1. Data based on characterization results, not tested in production.

Figure 16: DFSDM timing diagram



6.3.26 Timer characteristics

The parameters given in the following tables are guaranteed by design.

Refer to [Section 6.3.14: I/O port characteristics](#) for details on the input/output alternate function characteristics (output compare, input capture, external clock, PWM output).

SPI characteristics

Unless otherwise specified, the parameters given in [Table 84](#) for SPI are derived from tests performed under the ambient temperature, f_{PCLKx} frequency and supply voltage conditions summarized in [Table 22: General operating conditions](#).

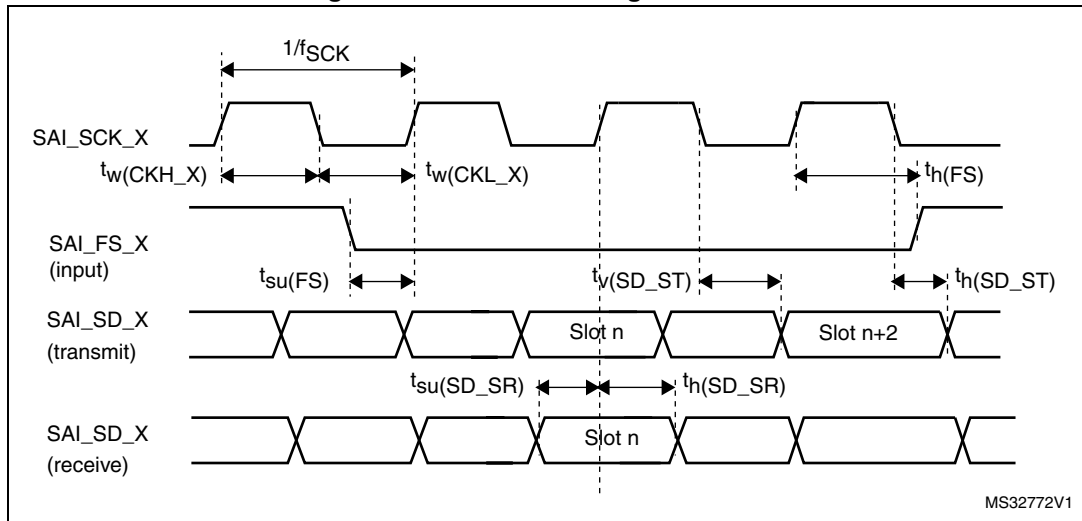
- Output speed is set to $OSPEEDRy[1:0] = 11$
- Capacitive load $C = 30$ pF
- Measurement points are done at CMOS levels: $0.5 \times V_{DD}$

Refer to [Section 6.3.14: I/O port characteristics](#) for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO for SPI).

Table 84. SPI characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{SCK} $1/t_{c(SCK)}$	SPI clock frequency	Master mode receiver/full duplex $2.7 < V_{DD} < 3.6$ V Voltage Range 1	-	-	24	MHz
		Master mode receiver/full duplex $1.71 < V_{DD} < 3.6$ V Voltage Range 1			13	
		Master mode transmitter $1.71 < V_{DD} < 3.6$ V Voltage Range 1			40	
		Slave mode receiver $1.71 < V_{DD} < 3.6$ V Voltage Range 1			40	
		Slave mode transmitter/full duplex $2.7 < V_{DD} < 3.6$ V Voltage Range 1			26 ⁽²⁾	
		Slave mode transmitter/full duplex $1.71 < V_{DD} < 3.6$ V Voltage Range 1			16 ⁽²⁾	
		Voltage Range 2			13	
		$1.08 < V_{DDIO2} < 1.32$ V ⁽³⁾			8	
$t_{su(NSS)}$	NSS setup time	Slave mode, SPI prescaler = 2	$4 \times T_{PCLK}$	-	-	ns
$t_{h(NSS)}$	NSS hold time	Slave mode, SPI prescaler = 2	$2 \times T_{PCLK}$	-	-	ns
$t_{w(SCKH)}$ $t_{w(SCKL)}$	SCK high and low time	Master mode	$T_{PCLK} - 2$	T_{PCLK}	$T_{PCLK} + 2$	ns
$t_{su(MI)}$	Data input setup time	Master mode	3.5	-	-	ns
$t_{su(SI)}$		Slave mode	3	-	-	
$t_{h(MI)}$	Data input hold time	Master mode	6.5	-	-	ns
$t_{h(SI)}$		Slave mode	3	-	-	
$t_{a(SO)}$	Data output access time	Slave mode	9	-	36	ns
$t_{dis(SO)}$	Data output disable time	Slave mode	9	-	16	ns

Figure 34. SAI slave timing waveforms



MS32772V1

SDMMC characteristics

Unless otherwise specified, the parameters given in [Table 88](#) for SDIO are derived from tests performed under the ambient temperature, f_{PCLKx} frequency and V_{DD} supply voltage conditions summarized in [Table 22: General operating conditions](#), with the following configuration:

- Output speed is set to $OSPEEDRy[1:0] = 11$
- Capacitive load $C = 30$ pF
- Measurement points are done at CMOS levels: $0.5 \times V_{DD}$

Refer to [Section 6.3.14: I/O port characteristics](#) for more details on the input/output characteristics.

Table 88. SD / MMC dynamic characteristics, $V_{DD}=2.7$ V to 3.6 V⁽¹⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{PP}	Clock frequency in data transfer mode	-	0	-	50	MHz
-	SDIO_CK/fPCLK2 frequency ratio	-	-	-	4/3	-
$t_{W(CKL)}$	Clock low time	$f_{PP} = 50$ MHz	8	10	-	ns
$t_{W(CKH)}$	Clock high time	$f_{PP} = 50$ MHz	8	10	-	ns
CMD, D inputs (referenced to CK) in MMC and SD HS mode						
t_{ISU}	Input setup time HS	$f_{PP} = 50$ MHz	2	-	-	ns
t_{IH}	Input hold time HS	$f_{PP} = 50$ MHz	4.5	-	-	ns
CMD, D outputs (referenced to CK) in MMC and SD HS mode						
t_{OV}	Output valid time HS	$f_{PP} = 50$ MHz	-	12	14	ns
t_{OH}	Output hold time HS	$f_{PP} = 50$ MHz	9	-	-	ns
CMD, D inputs (referenced to CK) in SD default mode						
t_{ISUD}	Input setup time SD	$f_{PP} = 50$ MHz	2	-	-	ns
t_{IHD}	Input hold time SD	$f_{PP} = 50$ MHz	4.5	-	-	ns

Table 94. Asynchronous non-multiplexed SRAM/PSRAM/NOR write-NWAIT timings⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	$8T_{HCLK}+0.5$	$8T_{HCLK}+0.5$	ns
$t_{w(NWE)}$	FMC_NWE low time	$6T_{HCLK}-0.5$	$6T_{HCLK}+0.5$	
$t_{su(NWAIT_NE)}$	FMC_NWAIT valid before FMC_NEx high	$6T_{HCLK}+2$	-	
$t_{h(NE_NWAIT)}$	FMC_NEx hold time after FMC_NWAIT invalid	$4T_{HCLK}+2$	-	

1. CL = 30 pF.

2. Guaranteed by characterization results.

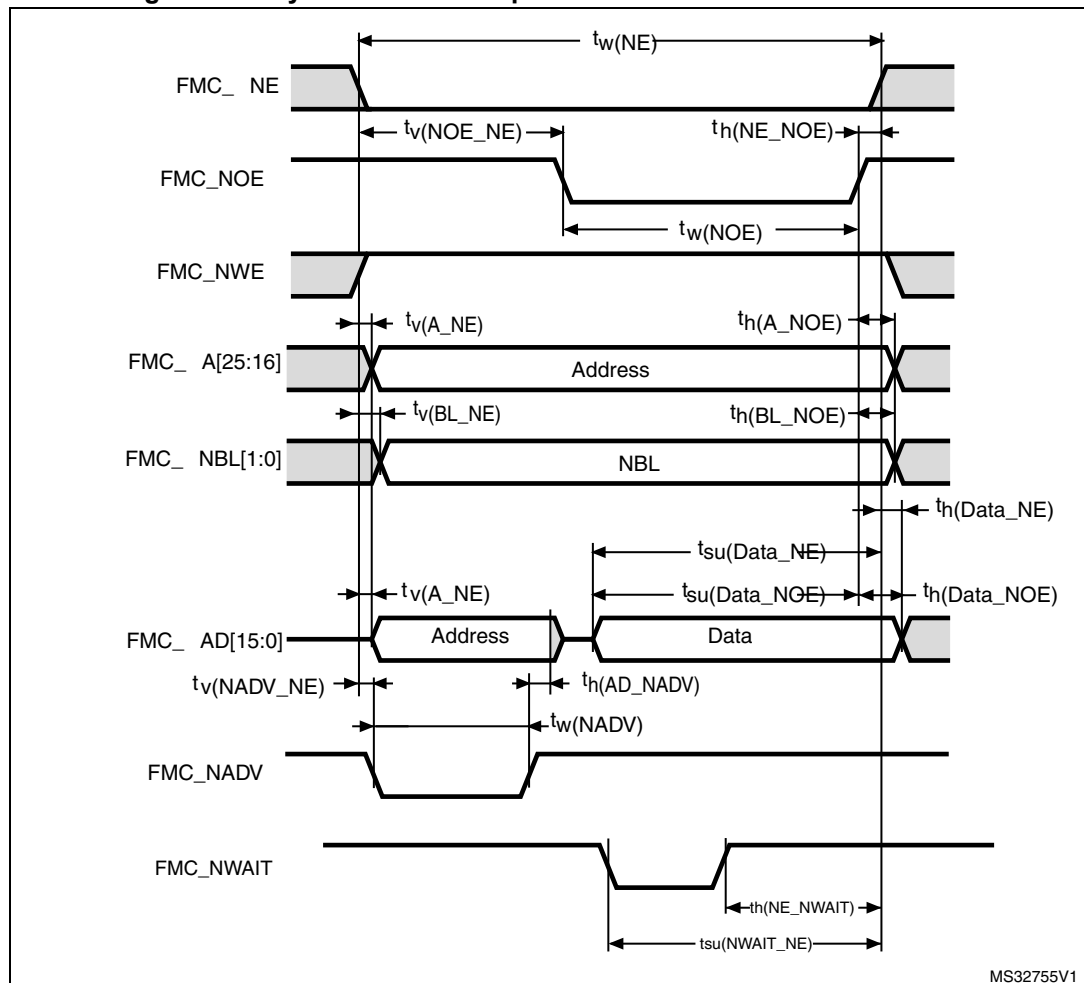
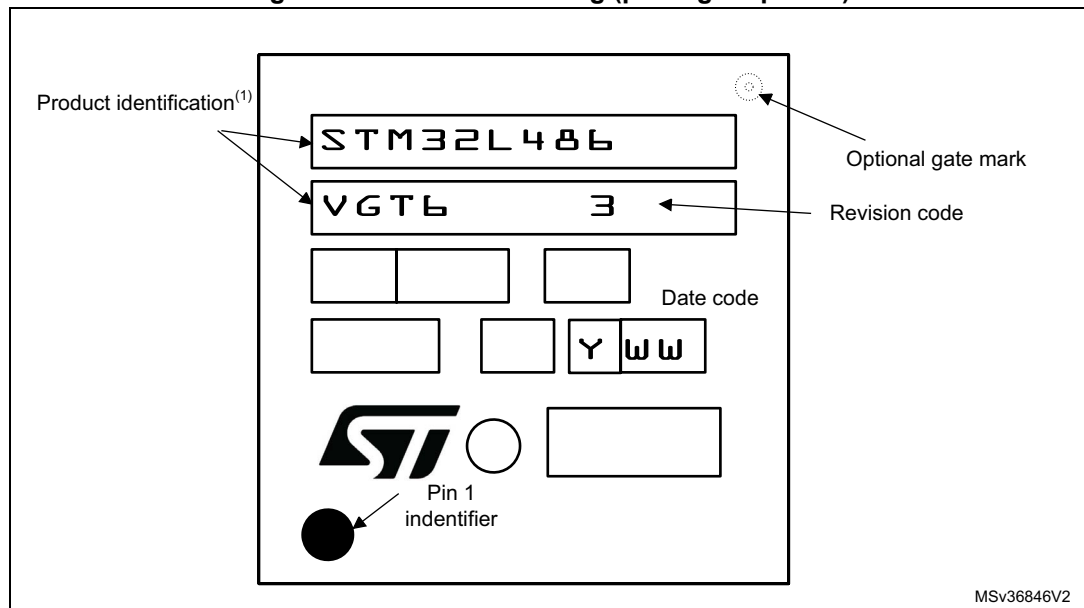
Figure 39. Asynchronous multiplexed PSRAM/NOR read waveforms

Figure 57. LQFP100 marking (package top view)



1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

Table 110. WLCSP72 - 72-ball, 4.4084 x 3.7594 mm, 0.4 mm pitch wafer level chip scale package mechanical data (continued)

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
G	-	0.2797	-	-	0.0110	-
aaa	-	0.100	-	-	0.0039	-
bbb	-	0.100	-	-	0.0039	-
ccc	-	0.100	-	-	0.0039	-
ddd	-	0.050	-	-	0.0020	-
eee	-	0.050	-	-	0.0020	-

1. Values in inches are converted from mm and rounded to 4 decimal digits.
2. Back side coating
3. Dimension is measured at the maximum bump diameter parallel to primary datum Z.

Figure 59. WLCSP72 - 72-ball, 4.4084 x 3.7594 mm, 0.4 mm pitch wafer level chip scale package recommended footprint

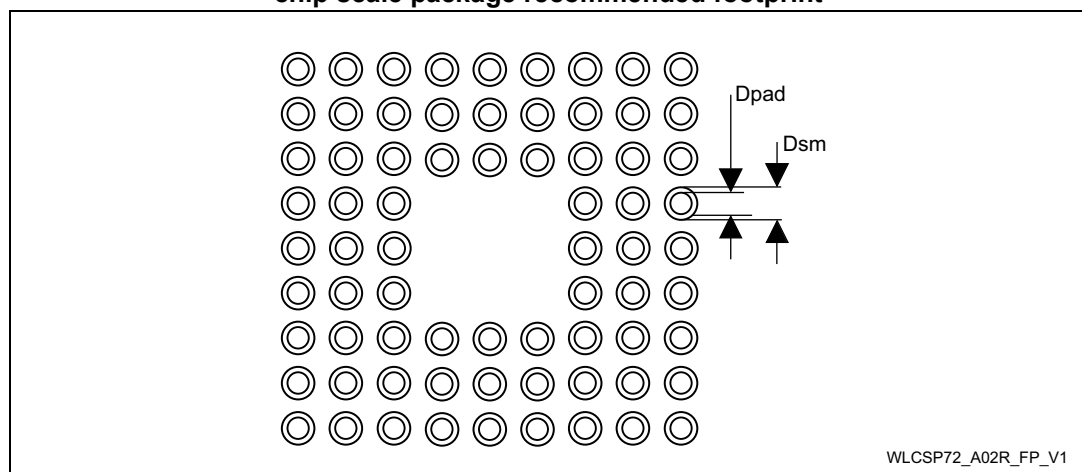


Table 111. WLCSP72 recommended PCB design rules (0.4 mm pitch BGA)

Dimension	Recommended values
Pitch	0.4 mm
Dpad	0.225 mm
Dsm	0.290 mm typ. (depends on the solder mask registration tolerance)
Stencil opening	0.250 mm
Stencil thickness	0.100 mm